

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _A = +25°C
-30V	45mΩ @ V _{GS} = -10V	-4.3A
	65mΩ @ V _{GS} = -4.5V	-3.3A

Description

This new generation MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

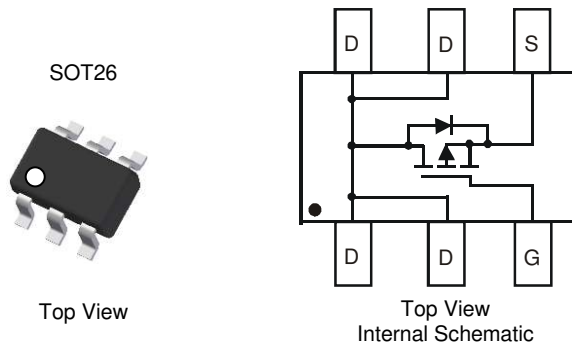
- General purpose interfacing switches
- Power management functions
- Analog switches

Features

- Low Gate Threshold Voltage
- Low On-Resistance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.** <https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: SOT26
- Package Material – Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.016 grams (Approximate)

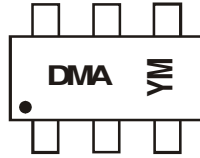


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP3056LDM-7	SOT26	3000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



DMA = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: J = 2022)
 M = Month (ex: 8 = August)

Date Code Key

Year	2008	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	V	J	K	L	M	N	O	P	R	S	T
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-30	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = -10V	Steady State T _A = +25°C	I _D	-4.3
	t < 10s T _A = +25°C	I _D	-5.8
Maximum Continuous Body Diode Forward Current (Note 5)	I _S	-2.3	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-13	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6) T _A = +25°C	P _D	1.25	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State	R _{θJA}	100	°C/W
Total Power Dissipation (Note 5) T _A = +25°C	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 5) Steady State	R _{θJA}	86	°C/W
Thermal Resistance, Junction to Case	R _{θJC}	15.6	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
STATIC PARAMETERS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	T _J = +25°C V _{GS} = 0V, V _{DS} = -30V
Gate-Body Leakage Current	I _{GSS}	—	—	±100 ±800	nA	V _{GS} = ±20V, V _{DS} = 0V V _{GS} = ±25V, V _{DS} = 0V
Gate Threshold Voltage	V _{GS(TH)}	-1.0	—	-2.1	V	V _{GS} = V _{DS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	45 65	mΩ	V _{GS} = -10V, I _D = -5A V _{GS} = -4.5V, I _D = -4.2A
Forward Transconductance	g _{FS}	—	8	—	s	V _{DS} = -10V, I _D = -4.3A
Diode Forward Voltage	V _{SD}	—	—	-1.2	V	V _{GS} = 0V, I _S = -1.7A
DYNAMIC PARAMETERS (Note 8)						
Input Capacitance	C _{iss}	—	948	—	pF	V _{GS} = 0V, V _{DS} = -25V f = 1.0MHz
Output Capacitance	C _{oss}	—	105	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	100	—	pF	
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	Q _g	—	10.1	—	nC	V _{DS} = -15V, V _{GS} = -4.5V I _D = -6A
	Q _g	—	21.1	—	nC	
Gate-Source Charge	Q _{gs}	—	2.8	—		V _{DS} = -15V, V _{GS} = -10V I _D = -6A
Gate-Drain Charge	Q _{gd}	—	3.2	—		
Gate Resistance	R _g	—	13.15	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Turn-On Delay Time	t _{D(ON)}	—	10.2	—	ns	V _{DS} = -15V, V _{GS} = -10V I _D = -1A, R _g = 6.0Ω
Rise Time	t _r	—	6.6	—		
Turn-Off Delay Time	t _{D(OFF)}	—	50.1	—		
Fall Time	t _f	—	22.3	—		

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

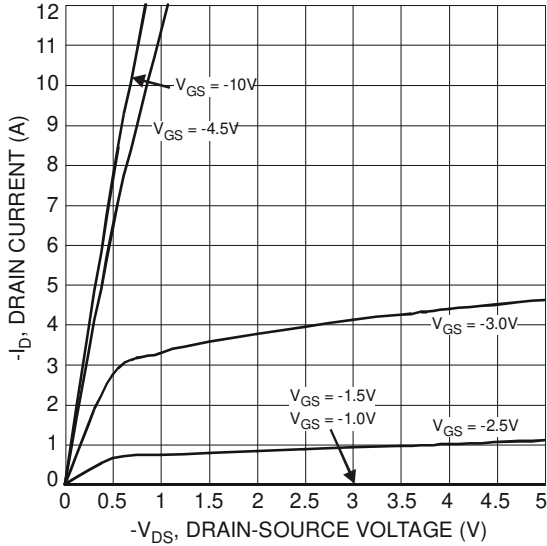


Fig. 1 Typical Output Characteristics

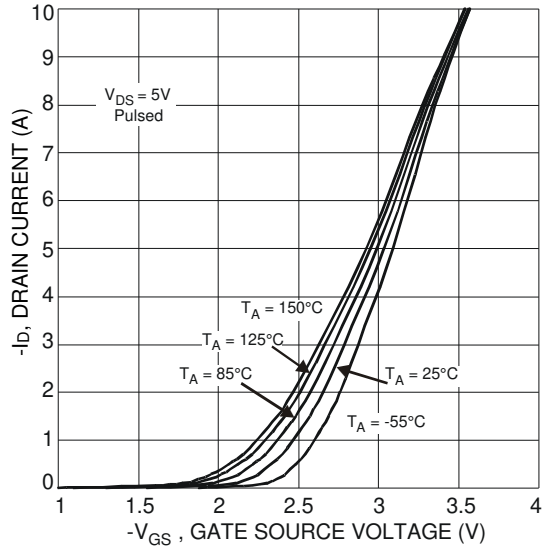


Fig. 2 Typical Transfer Characteristics

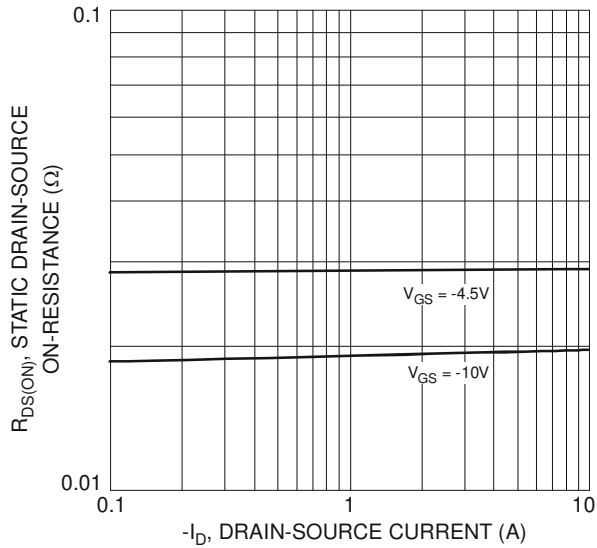


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

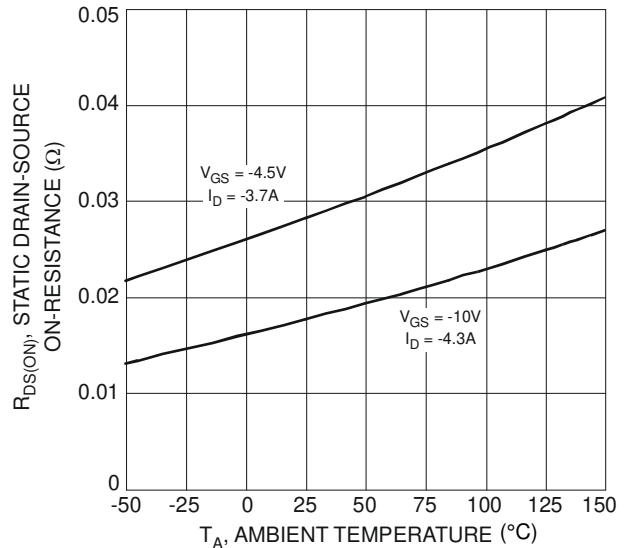


Fig. 4 Static Drain-Source On-Resistance vs. Ambient Temperature

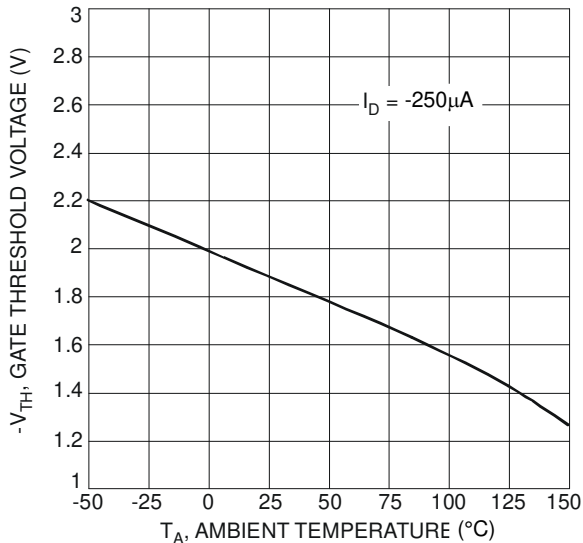


Fig. 5 Gate Threshold Variation vs. Ambient Temperature

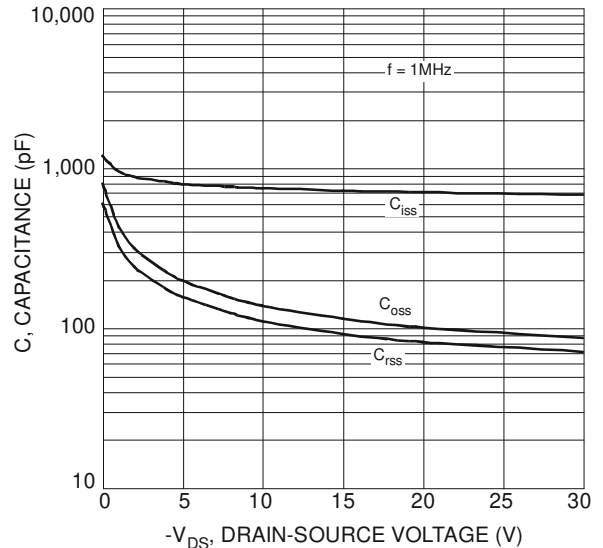


Fig. 6 Typical Total Capacitance

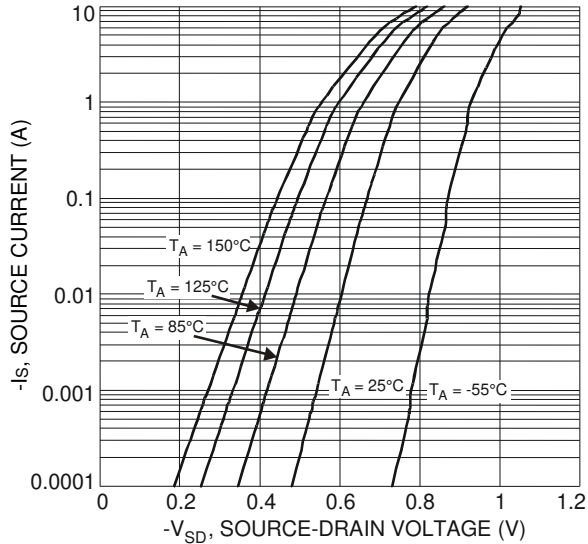


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

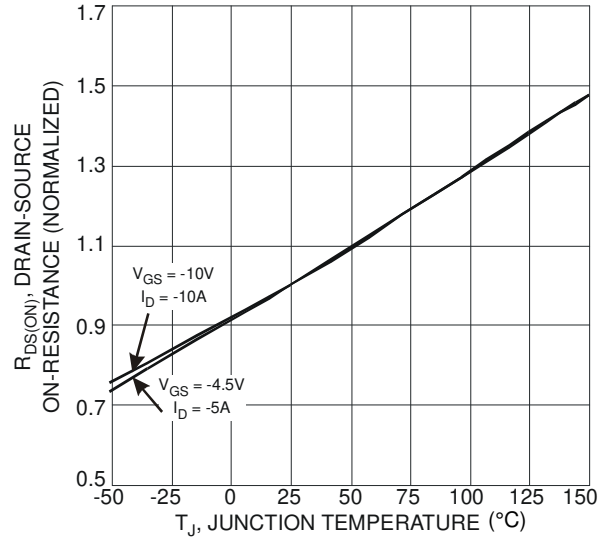


Fig. 8 On-Resistance Variation with Temperature

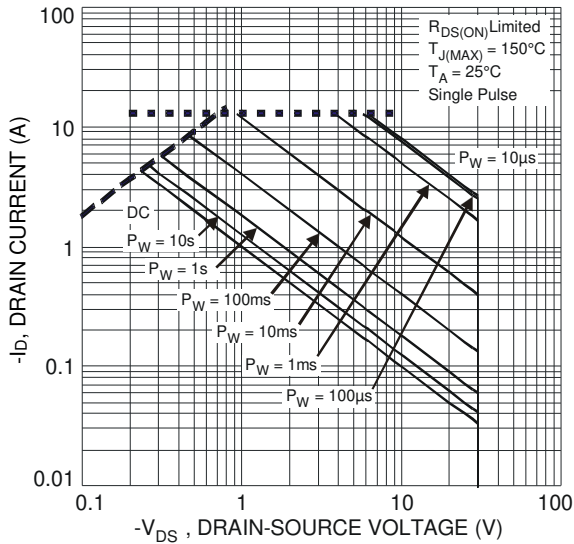


Fig. 9 Safe Operation Area

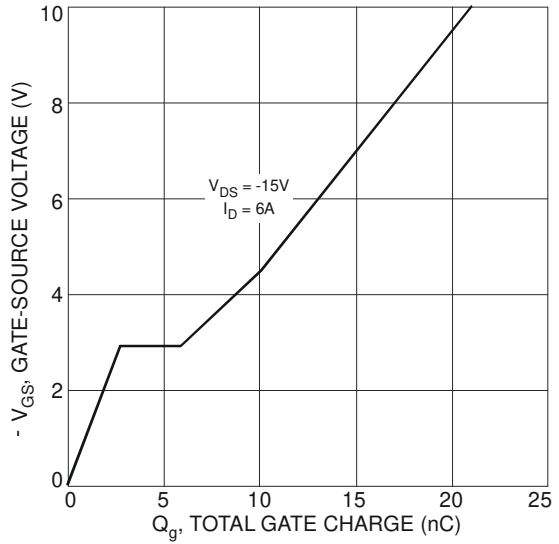


Fig. 10 Gate-Charge Characteristics

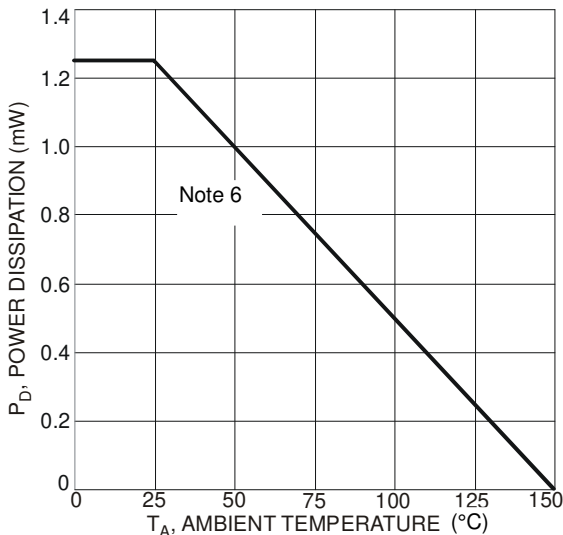


Fig. 11 Power Dissipation vs. Ambient Temperature

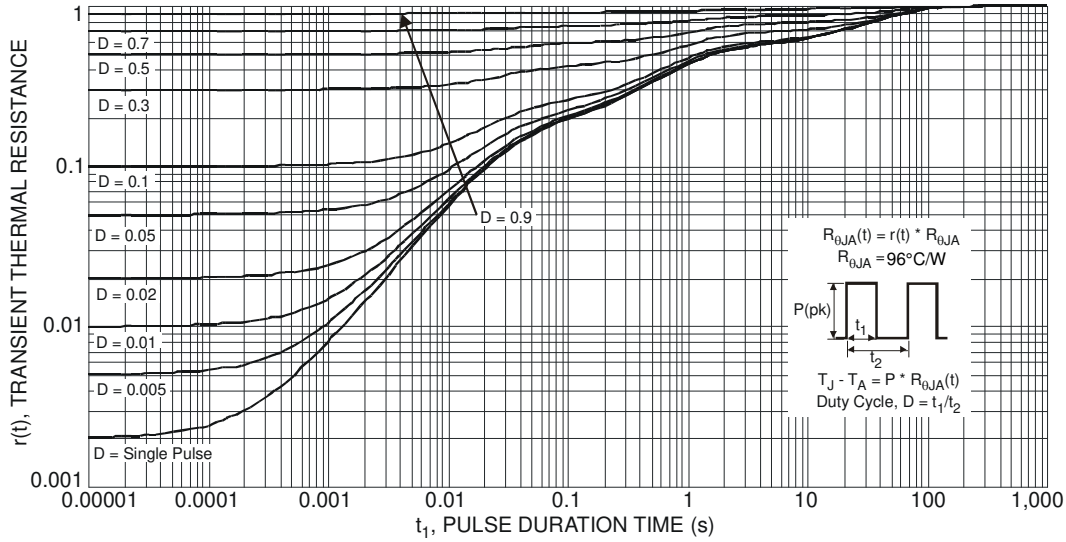
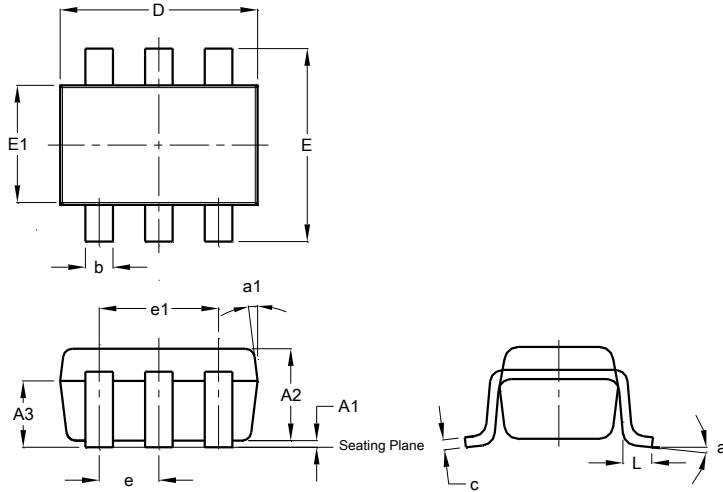


Fig. 12 Transient Thermal Response

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT26

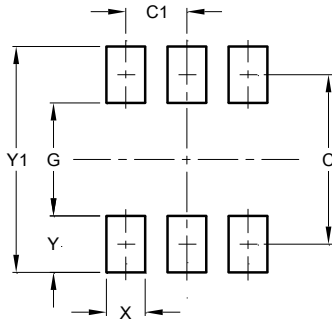


SOT26			
Dim	Min	Max	Typ
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT26



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20

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